# Quad. 2-input NAND Gates

# HITACHI

ADE-205-240 (Z) 1st Edition March 1999

### Description

The HD74LV00A has four two-input NAND gates in a 14-pin package. Low-voltage and high-speed operation is suitable for the battery-powered products (e.g., notebook computers), and the low-power consumption extends the battery life.

### Features

- $V_{CC} = 2.0 \text{ V}$  to 5.5 V operation
- All inputs  $V_{IH}$  (Max.) = 5.5 V (@V<sub>CC</sub> = 0 V to 5.5 V)
- All outputs  $V_0$  (Max.) = 5.5 V (@V<sub>CC</sub> = 0 V)
- Typical  $V_{OL}$  ground bounce < 0.8 V (@V<sub>CC</sub> = 3.3 V, Ta = 25°C)
- Typical  $V_{OH}$  undershoot > 2.3 V (@V<sub>CC</sub> = 3.3 V, Ta = 25°C)
- Output current  $\pm 6 \text{ mA}$  (@V<sub>cc</sub> = 3.0 V to 3.6 V),  $\pm 12 \text{ mA}$  (@V<sub>cc</sub> = 4.5 V to 5.5 V)

### **Function Table**

Inputs	
Α	

Α	В	Output Y
Н	Н	L
L	Х	Н
X	L	Н

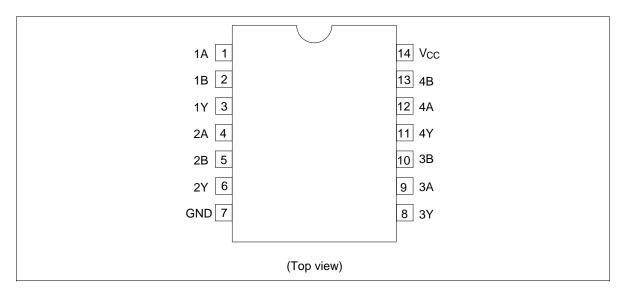
Note: H: High level

L: Low level

X: Immaterial



# **Pin Arrangement**



### **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V <sub>cc</sub>	-0.5 to 7.0	V	
Input voltage range*1	V	-0.5 to 7.0	V	
Output voltage range*1,2	Vo	-0.5 to V <sub>cc</sub> + 0.5	V	Output: H or L
		-0.5 to 7.0		V <sub>cc</sub> : OFF
Input clamp current	I <sub>IK</sub>	-20	mA	V <sub>1</sub> < 0
Output clamp current	Ι <sub>οκ</sub>	±50	mA	$V_{\rm o}$ < 0 or $V_{\rm o}$ > $V_{\rm cc}$
Continuous output current	I <sub>o</sub>	±25	mA	$V_{o} = 0$ to $V_{cc}$
Continuous current through $V_{cc}$ or GND	$I_{\rm CC}$ or $I_{\rm GND}$	±50	mA	
Maximum power dissipation at Ta = $25^{\circ}$ C (in still air)* <sup>3</sup>	P <sub>T</sub>	785	mW	SOP
		500		TSSOP
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 5.5 V maximum.

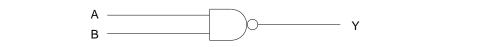
3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

# **Recommended Operating Conditions**

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V <sub>cc</sub>	2.0	5.5	V	
Input voltage range	V	0	5.5	V	
Output voltage range	Vo	0	V <sub>cc</sub>	V	
Output current	I <sub>OH</sub>	_	-50	μA	$V_{cc} = 2.0 V$
		_	-2	mA	$V_{cc}$ = 2.3 to 2.7 V
		_	-6		$V_{cc}$ = 3.0 to 3.6 V
		_	-12		$V_{cc}$ = 4.5 to 5.5 V
	I <sub>ol</sub>	_	50	μA	$V_{cc} = 2.0 V$
		_	2	mA	$V_{cc}$ = 2.3 to 2.7 V
		_	6		$V_{cc}$ = 3.0 to 3.6 V
		_	12		$V_{cc}$ = 4.5 to 5.5 V
Input transition rise or fall rate	$\Delta t / \Delta v$	0	200	ns/V	$V_{cc}$ = 2.3 to 2.7 V
		0	100		$V_{cc}$ = 3.0 to 3.6 V
		0	20		$V_{cc}$ = 4.5 to 5.5 V
Operating free-air temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

# Logic Diagram



## **DC Electrical Characteristics**

#### • Ta = -40 to $85^{\circ}C$

Item	Symbol	V <sub>cc</sub> (V)*	Min	Тур	Max	Unit	Test Conditions
Input voltage	V <sub>IH</sub>	2.0	1.5	_	—	V	
		2.3 to 2.7	$V_{CC}  imes 0.7$	_	—	_	
		3.0 to 3.6	$V_{CC}  imes 0.7$	_	_	_	
		4.5 to 5.5	$V_{CC}  imes 0.7$	_	_	_	
	V <sub>IL</sub>	2.0	_	_	0.5	_	
		2.3 to 2.7	_	_	$V_{CC}  imes 0.3$	_	
		3.0 to 3.6	_	_	$V_{CC}  imes 0.3$	_	
		4.5 to 5.5	_	_	$V_{cc}  imes 0.3$	_	
Output voltage	V <sub>OH</sub>	Min to Max	V <sub>cc</sub> - 0.1	—	—	V	I <sub>OH</sub> = -50 μA
		2.3	2.0	_	_	_	$I_{OH} = -2 \text{ mA}$
		3.0	2.48	_	_	_	I <sub>OH</sub> = -6 mA
		4.5	3.8	_	_	_	I <sub>OH</sub> = -12 mA
	V <sub>OL</sub>	Min to Max	_	—	0.1		I <sub>OL</sub> = 50 μA
		2.3	_	_	0.4	_	I <sub>OL</sub> = 2 mA
		3.0	_	_	0.44	_	I <sub>OL</sub> = 6 mA
		4.5	_	_	0.55	_	I <sub>OL</sub> = 12 mA
Input current	I <sub>IN</sub>	0 to 5.5	_	_	±1	μΑ	$V_{IN} = 5.5 V \text{ or GND}$
Quiescent supply current	I <sub>cc</sub>	5.5	_	_	20	μA	$V_{IN} = V_{CC}$ or GND, $I_0 = 0$
Output leakage current	I <sub>OFF</sub>	0	_	—	5	μA	V <sub>0</sub> = 5.5 V
Input capacitance	C <sub>IN</sub>	3.3	_	3.3	_	pF	$V_1 = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

# **Switching Characteristics**

### • $V_{CC} = 2.5 \pm 0.2 V$

		Ta = 25°C Ta = -40 to 85°C								
ltem	Symbol	Min	Тур	Мах	Min	Max	Unit	Test Conditions	FROM (Input)	TO (Output)
Propagation	t <sub>PLH</sub>	—	7.1	12.9	1.0	15.0	ns	C <sub>L</sub> = 15 pF	A or B	Y
delay time	t <sub>PHL</sub>	_	9.6	16.6	1.0	20.0		C <sub>L</sub> = 50 pF	-	

### • $V_{CC} = 3.3 \pm 0.3 V$

		Ta =	25°C		Ta = − 85°C	40 to				
ltem	Symbol	Min	Тур	Max	Min	Мах	Unit	Test Conditions	FROM (Input)	TO (Output)
Propagation	t <sub>PLH</sub>	—	5.0	7.9	1.0	9.5	ns	C <sub>L</sub> = 15 pF	A or B	Y
delay time	t <sub>PHL</sub>	_	6.9	11.4	1.0	13.0	_	C <sub>L</sub> = 50 pF	-	

•  $V_{CC} = 5.0 \pm 0.5 \text{ V}$ 

		Ta =	25°C		Ta = –₄ 85°C	40 to				
ltem	Symbol	Min	Тур	Мах	Min	Мах	Unit	Test Conditions	FROM (Input)	TO (Output)
Propagation	t <sub>PLH</sub>	_	3.6	5.5	1.0	6.5	ns	C <sub>L</sub> = 15 pF	A or B	Y
delay time	t <sub>PHL</sub>	_	4.9	7.5	1.0	8.5		C <sub>L</sub> = 50 pF	-	

# **Operating Characteristics**

•  $C_L = 50 \text{ pF}$ 

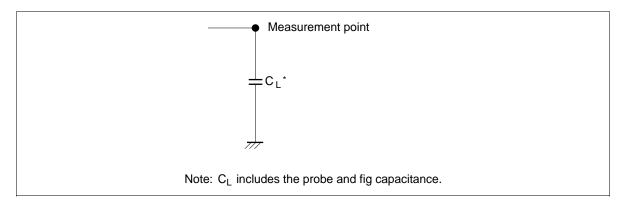
			Ta = 25°	Ta = 25°C			
ltem	Symbol	V <sub>cc</sub> (V)	Min	Тур	Max	Unit	Test Conditions
Power dissipation capacitance	C <sub>PD</sub>	3.3	_	9.5	_	pF	f = 10 MHz
		5.0	—	11.0	_		

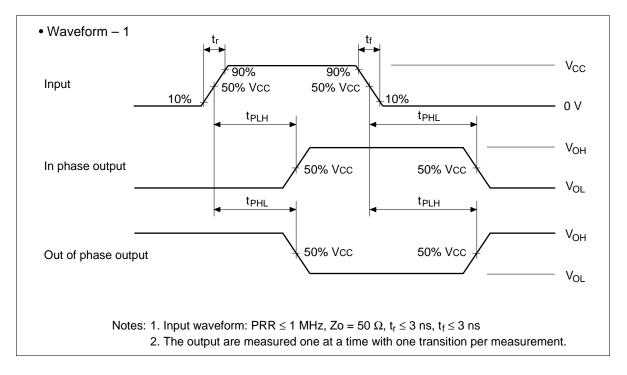
## **Noise Characteristics**

•  $C_L = 50 \text{ pF}$ 

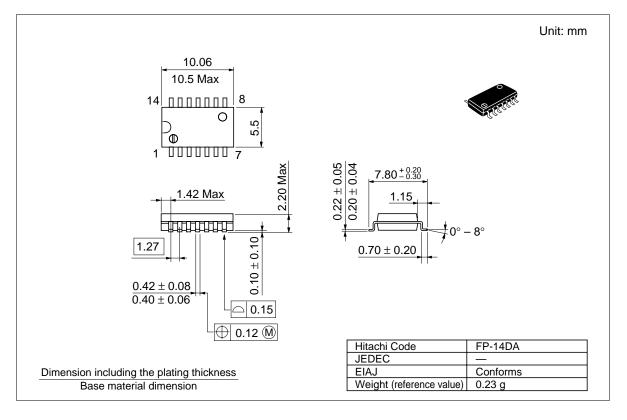
_			Ta = 25°C	2			
ltem	Symbol	V <sub>cc</sub> (V)	Min	Тур	Max	Unit	Test Conditions
Quiet output, maximum dynamic V <sub>oL</sub>	$V_{\text{OL}(\text{P})}$	3.3	_	0.2	0.8	V	
Quiet output, minimum dynamic V <sub>oL</sub>	$V_{\text{OL}(V)}$	3.3	_	-0.1	-0.8		
Quiet output, minimum dynamic V <sub>он</sub>	$V_{OH(V)}$	3.3	_	3.1	—		
High-level dynamic input voltage	V <sub>IH (D)</sub>	3.3	2.31	_	_	V	
Low-level dynamic inout voltage	$V_{\text{IL}(D)}$	3.3	_	_	0.99		

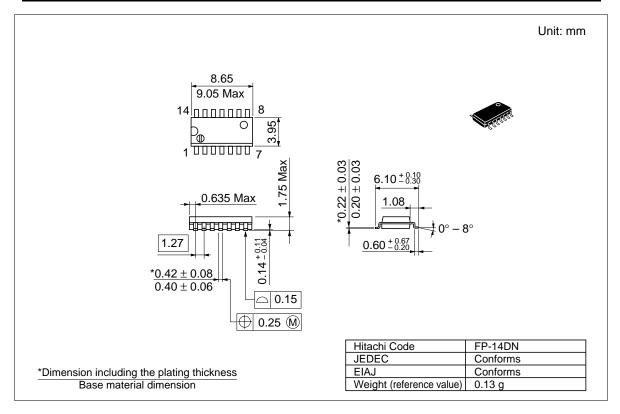
### **Test Circuit**

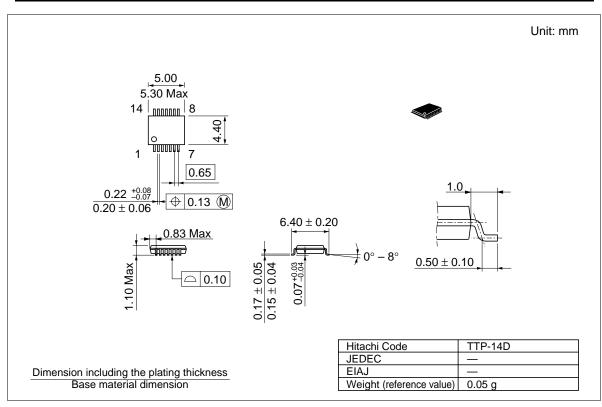




### **Package Dimensions**







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